International
IOR Rectifier

PD - 95531

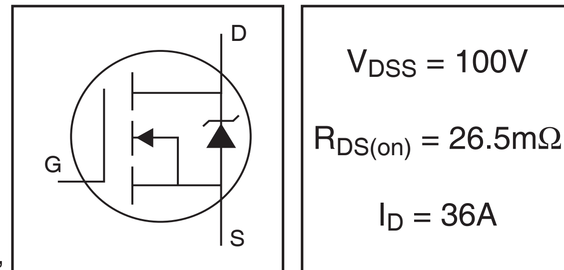
AUTOMOTIVE MOSFET

IRF540ZPbF
IRF540ZSPbF
IRF540ZLPbF

HEXFET® Power MOSFET

Features

- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free



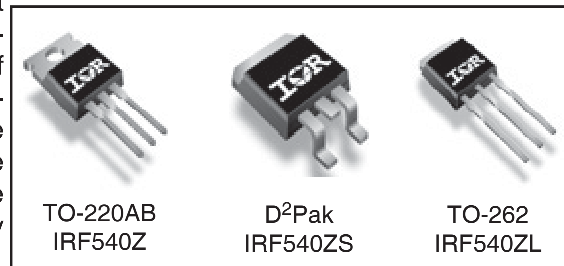
V_{DSS} = 100V

$R_{DS(on)}$ = 26.5mΩ

I_D = 36A

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating . These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



TO-220AB	D²Pak	TO-262
IRF540Z	IRF540ZS	IRF540ZL

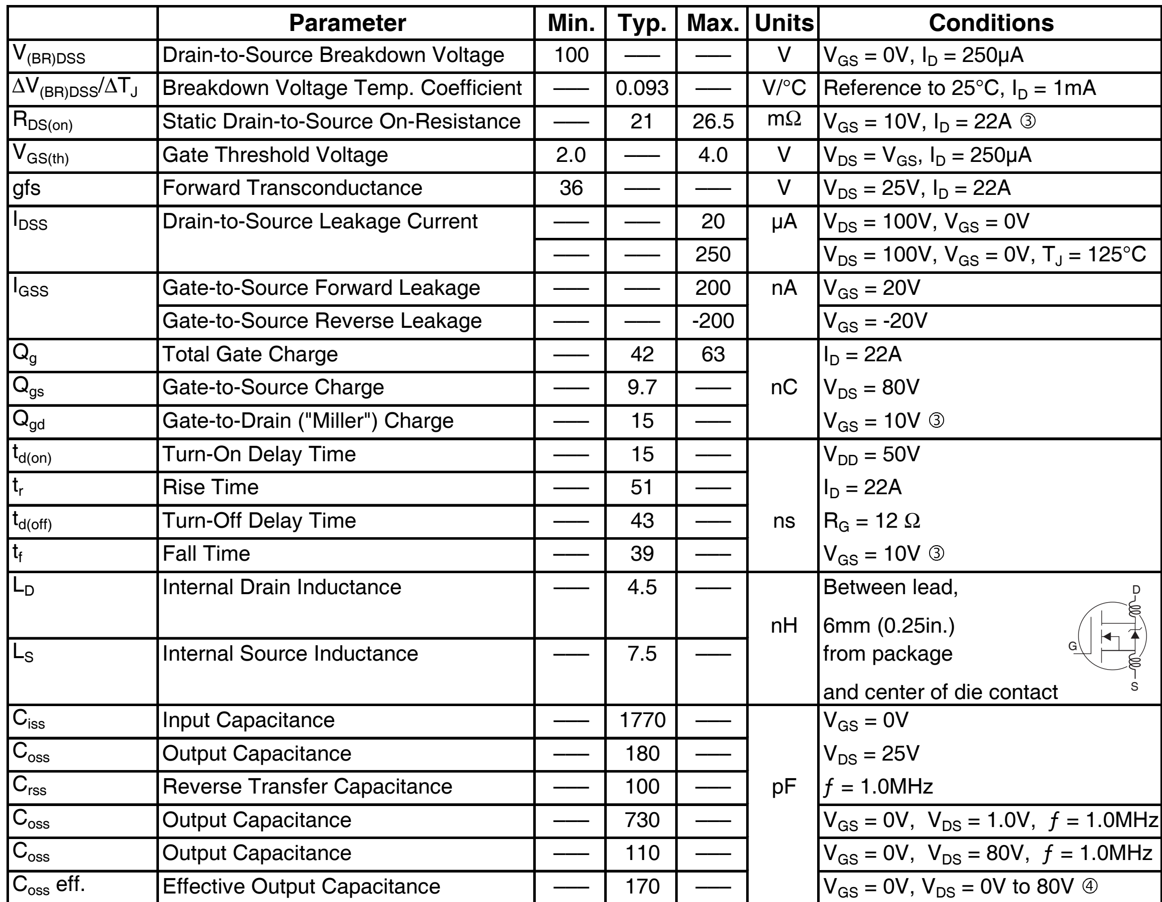
Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	36	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	25	
I_{DM}	Pulsed Drain Current ①	140	
P_D @T_C = 25°C	Power Dissipation	92	W
	Linear Derating Factor	0.61	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy②	83	mJ
E_{AS} (Tested)	Single Pulse Avalanche Energy Tested Value ⑥	120	
I_{AR}	Avalanche Current ①	See Fig.12a, 12b, 15, 16	A
E_{AR}	Repetitive Avalanche Energy ⑤		mJ
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw ⑦	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{θJC}$	Junction-to-Case	——	1.64	°C/W
$R_{θCS}$	Case-to-Sink, Flat Greased Surface ⑦	0.50	——	
$R_{θJA}$	Junction-to-Ambient ⑦	——	62	
$R_{θJA}$	Junction-to-Ambient (PCB Mount) ⑧	——	40	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

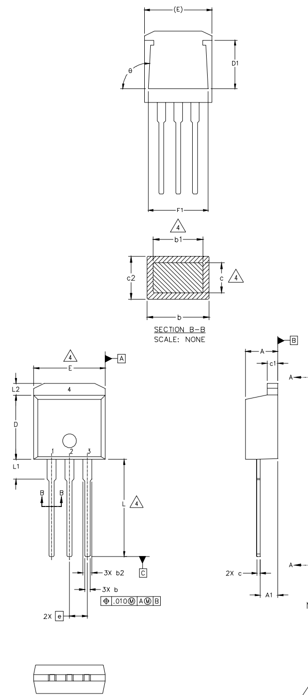


	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.093	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	21	26.5	mΩ	V_{GS} = 10V, I_D = 22A ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}$, I_D = 250μA
gfs	Forward Transconductance	36	—	—	V	V_{DS} = 25V, I_D = 22A
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V_{DS} = 100V, V_{GS} = 0V
		—	—	250		V_{DS} = 100V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-200		V_{GS} = -20V
Q_g	Total Gate Charge	—	42	63		I_D = 22A
Q_{gs}	Gate-to-Source Charge	—	9.7	—	nC	V_{DS} = 80V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	15	—		V_{GS} = 10V ③
$t_{d(on)}$	Turn-On Delay Time	—	15	—		V_{DD} = 50V
t_r	Rise Time	—	51	—		I_D = 22A
$t_{d(off)}$	Turn-Off Delay Time	—	43	—	ns	R_G = 12 Ω
t_f	Fall Time	—	39	—		V_{GS} = 10V ③
L_D	Internal Drain Inductance	—	4.5	—		Between lead,
					nH	6mm (0.25in.)
L_S	Internal Source Inductance	—	7.5	—		from package
						and center of die contact
C_{iss}	Input Capacitance	—	1770	—		V_{GS} = 0V
C_{oss}	Output Capacitance	—	180	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	100	—	pF	f = 1.0MHz
C_{oss}	Output Capacitance	—	730	—		V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz
C_{oss}	Output Capacitance	—	110	—		V_{GS} = 0V, V_{DS} = 80V, f = 1.0MHz
C_{oss} eff.	Effective Output Capacitance	—	170	—		V_{GS} = 0V, V_{DS} = 0V to 80V ④

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	36	A	MOSFET symbol showing the
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	140		integral reverse p-n junction diode.
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C, I_S = 22A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	33	50	ns	T_J = 25°C, I_F = 22A, V_{DD} = 50V
Q_{rr}	Reverse Recovery Charge	—	41	62	nC	di/dt = 100A/μs ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

TO-262 Package Outline



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

HEXFET
1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

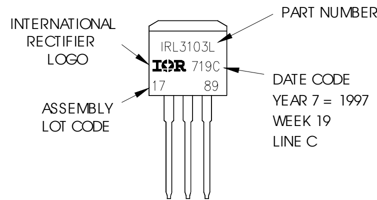
IGBT
1- GATE
2- COLLECTOR
3- EMITTER

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



OR